

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination LEE ET AL.	
		Examiner Savitri Mulpuri	Art Unit 2812	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-2004/0077156	04-2004	Tsakalakos et al.	438/479
	C	US-6,596,377	07-2003	Hersee et al.	428/312.2
	D	US-5,948,470	09-1999	Harrison et al.	427/198
	E	US-5,705,321	01-1998	Brueck et al.	430/316
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Saki et al, "Anew method of reducing dislocation density in GaN layer grown on sapphire subsatrtes by MOCVD" , Journal of Crystal Growth"221(200)334-337
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	W	Craven et al, "Threading location reduction via laterally overgrowth nonpolar a-plane GaN" Applied physics Letters" Vo. 81, No.7, 112/9/2002, pp 1201-1203
	X	Linthicum et al, 'Pendoepiaxy of GaN thin films", Applied Physcis Letters, vo.75, no.2, 12/7/1999, pp196-198.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.